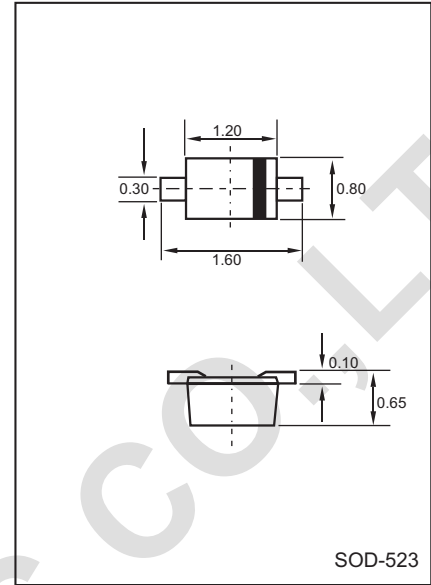


RB751S-40 Schottky barrier Diodes

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	30	mA
Peak forward surge current	I _{FSM}	200	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55~+125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			0.37	V	I _F =1mA
Reverse current	I _R			0.5	μ A	V _R =30V
Capacitance between terminals	C _T		2		pF	V _R =1V, f=1MHZ

● Electrical characteristic curves (Ta = 25°C)

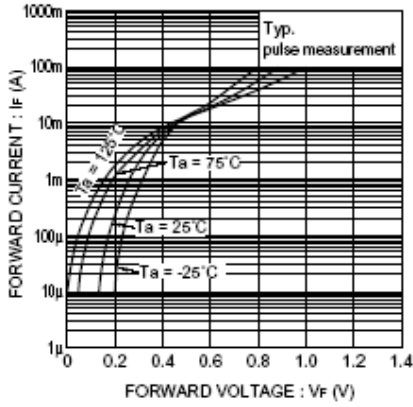


Fig. 1 Forward characteristics

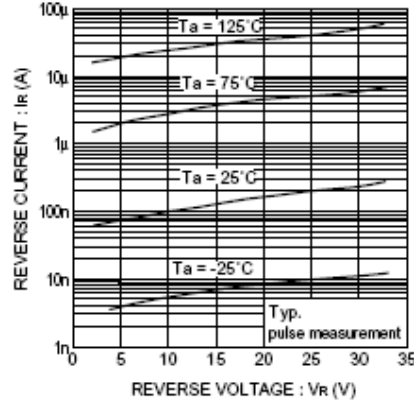


Fig. 2 Reverse characteristics

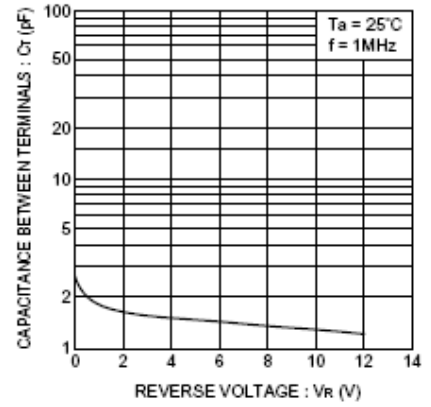


Fig. 3 Capacitance between terminals characteristics